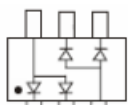
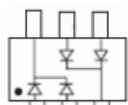


FEATURES

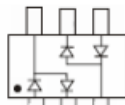
- Low Forward voltage drop
- Fast switching



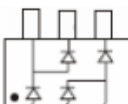
BAS40DW-06
Marking: K46



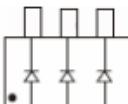
BAS40DW-05
Marking: K45



BAS40DW-04
Marking: K44

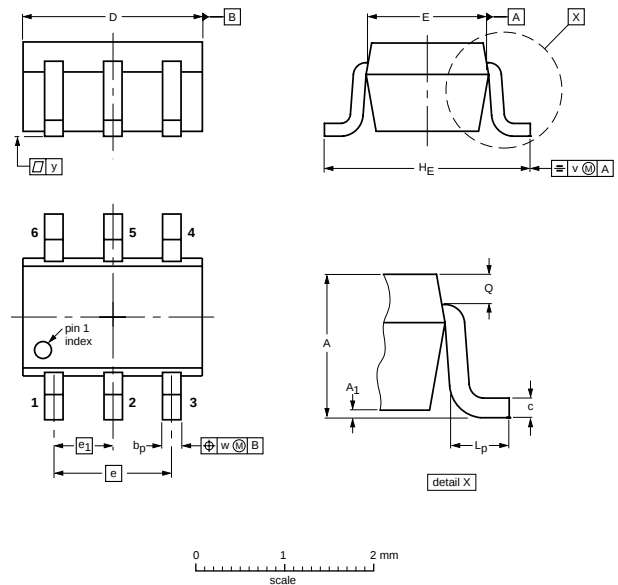


BAS40BRW
Marking: K47



BAS40TW
Marking: K43

SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	40	V
DC Blocking Voltage	V _R		
Average Rectified Output Current	I _O	200	mA
Power Dissipation	P _d	200	mW
Thermal Resistance. Junction to Ambient Air	R _{θJA}	625	°C/W
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-65-125	°C

BAS40TW_DW_04_05_06

Electrical Ratings @Ta=25°C

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R = 30V$		200	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Total capacitance	C_T	$V_R = 0, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = I_F = 1mA$ $R_L = 100\Omega$		5	ns

RATING AND CHARACTERISTIC CURVES (BAS40TW/DW 04 05 06)

